

MCP (Multi-Chip Package) FLASH MEMORY & SRAM CMOS

16M (× 8) FLASH MEMORY & 2M (× 8) STATIC RAM

MB84VA2100-10/MB84VA2101-10

■ FEATURES

- Power supply voltage of 2.7 to 3.6 V
- High performance
100 ns maximum access time
- Operating Temperature
-20 to +85°C

— FLASH MEMORY

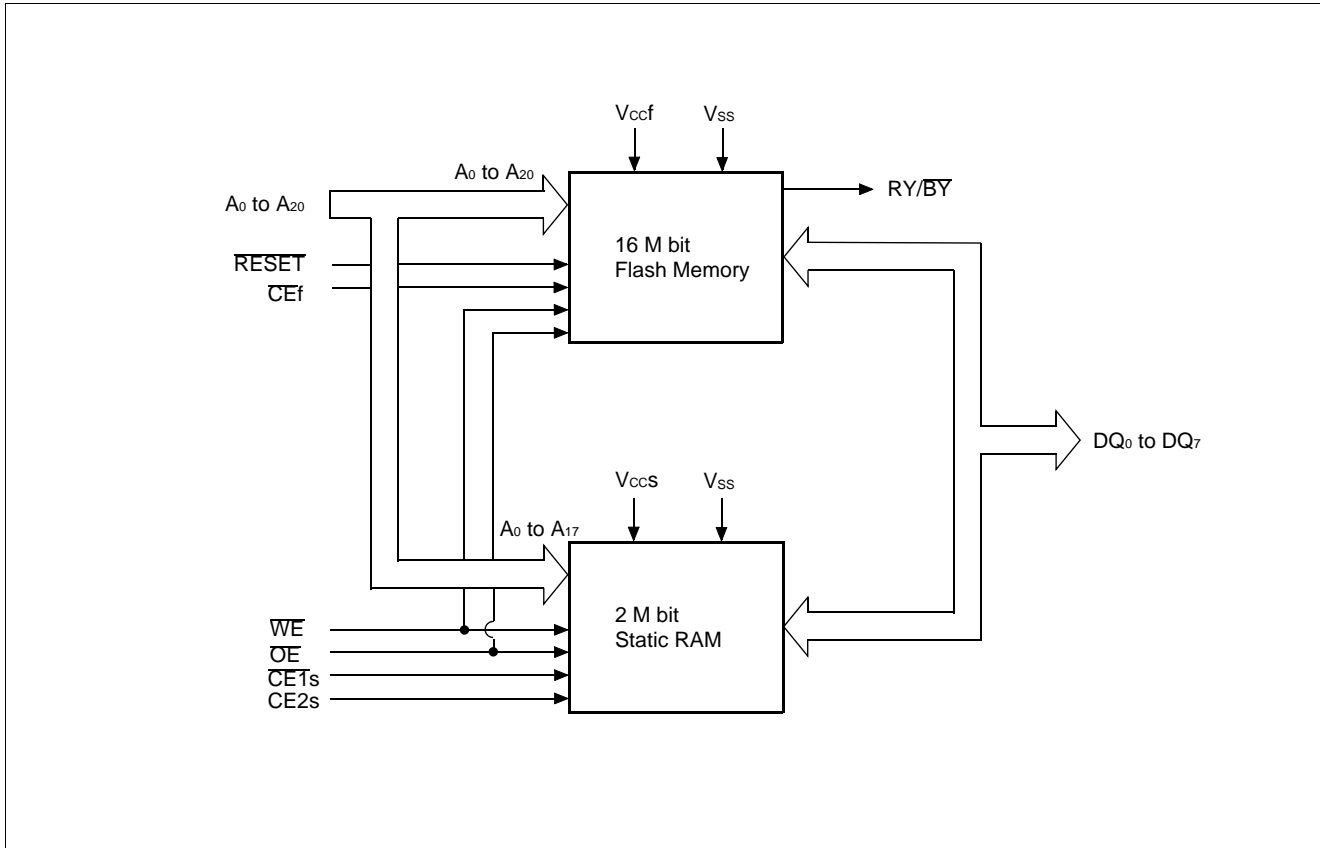
- Minimum 100,000 write/erase cycles
- Sector erase architecture
One 16 K byte, two 8 K bytes, one 32 K byte, and thirty one 64 K bytes.
Any combination of sectors can be concurrently erased. Also supports full chip erase.
- Boot Code Sector Architecture
MB84VA2100: Top sector
MB84VA2101: Bottom sector
- Embedded Erase™ Algorithms
Automatically pre-programs and erases the chip or any sector
- Embedded Program™ Algorithms
Automatically writes and verifies data at specified address
- Data Polling and Toggle Bit feature for detection of program or erase cycle completion
- Ready-Busy output (RY/BY)
Hardware method for detection of program or erase cycle completion
- Automatic sleep mode
When addresses remain stable, automatically switch themselves to low power mode.
- Low V_{cc} write inhibit ≤ 2.5 V
- Erase Suspend/Resume
Suspends the erase operation to allow a read in another sector within the same device
Please refer to "MBM29LV160T/B" data sheet in detailed function

— SRAM

- Power dissipation
Operating : 35 mA max.
Standby : 50 μA max.
- Power down features using $\overline{CE1}$ s and CE2s
- Data retention supply voltage: 2.0 V to 3.6 V

MB84VA2100-10/MB84VA2101-10

■ BLOCK DIAGRAM



■ PIN ASSIGNMENTS

(Top View)

| | A | B | C | D | E | F | G | H |
|---|-------------------|------------------|-----------------|------------------|-----------------|------------------|------------------|-----------------|
| 6 | $\overline{CE1s}$ | V _{SS} | DQ ₁ | A ₁ | A ₂ | A ₄ | CE _{2s} | A ₉ |
| 5 | A ₁₀ | DQ ₅ | DQ ₂ | A ₀ | A ₃ | A ₇ | RY/BY | A ₁₅ |
| 4 | \overline{OE} | DQ ₇ | DQ ₄ | DQ ₀ | A ₆ | A ₁₉ | RESET | A ₁₆ |
| 3 | A ₁₁ | A ₈ | A ₅ | N.C. | DQ ₃ | N.C. | A ₁₃ | A ₂₀ |
| 2 | A ₁₄ | A ₁₈ | N.C. | \overline{CEf} | N.C. | V _{ccf} | DQ ₆ | A ₁₂ |
| 1 | WE | V _{ccs} | A ₁₇ | V _{SS} | N.C. | N.C. | N.C. | N.C. |

Table 1 Pin Configuration

| Pin | Function | Input/ Output |
|------------------------------------|---|------------------|
| A ₀ to A ₁₇ | Address Inputs (Common) | I |
| A ₁₈ to A ₂₀ | Address Input (Flash) | I |
| DQ ₀ to DQ ₇ | Data Inputs/Outputs (Common) | I/O |
| \overline{CEf} | Chip Enable (Flash) | I |
| $\overline{CE1s}$ | Chip Enable (SRAM) | I |
| CE _{2s} | Chip Enable (SRAM) | I |
| \overline{OE} | Output Enable (Common) | I |
| WE | Write Enable (Common) | I |
| RY/BY | Ready/Busy Outputs (Flash) | O |
| RESET | Hardware Reset Pin/Sector Protection Unlock (Flash) | I |
| N.C. | No Internal Connection | — |
| V _{SS} | Device Ground (Common) | Power |
| V _{ccf} | Device Power Supply (Flash) | Power |
| V _{ccs} | Device Power Supply (SRAM) | Power |

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■ PRODUCT LINE UP

| | | Flash Memory | SRAM |
|---------------------------------------|--|-----------------------------|------|
| Ordering Part No. | $V_{CC} = 3.0\text{ V} \begin{matrix} +0.6\text{ V} \\ -0.3\text{ V} \end{matrix}$ | MB84VA2100-10/MB84VA2101-10 | |
| Max. Address Access Time (ns) | | 100 | 100 |
| Max. \overline{CE} Access Time (ns) | | 100 | 100 |
| Max. \overline{OE} Access Time (ns) | | 40 | 50 |

■ BUS OPERATIONS

Table 2 User Bus Operations

| Operation (1), (3) | \overline{CEf} | $\overline{CE1s}$ | $CE2s$ | \overline{OE} | \overline{WE} | DQ ₀ to DQ ₇ | RESET |
|----------------------|------------------|-------------------|--------|-----------------|-----------------|------------------------------------|-------|
| Full Standby | H | H | X | X | X | HIGH-Z | H |
| | | X | L | | | | |
| Output Disable | X | X | X | H | H | HIGH-Z | H |
| Read from Flash (2) | L | H | X | L | H | D _{OUT} | H |
| | | X | L | | | | |
| Write to Flash | L | H | X | H | L | D _{IN} | H |
| | | X | L | | | | |
| Read from SRAM | H | L | H | L | H | D _{OUT} | H |
| Write to SRAM | H | L | H | X | L | D _{IN} | H |
| Flash Hardware Reset | X | H | X | X | X | HIGH-Z | L |
| | | X | L | | | | |

Legend: L = V_{IL}, H = V_{IH}, X = V_{IL} or V_{IH}. See DC Characteristics for voltage levels.

- Notes:**
1. Other operations except for indicated this column are inhibited.
 2. \overline{WE} can be V_{IL} if \overline{OE} is V_{IL}, \overline{OE} at V_{IH} initiates the write operations.
 3. Do not apply $\overline{CEf} = V_{IL}$, $\overline{CE1s} = V_{IL}$ and $CE2s = V_{IH}$ at a time.

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■ FLEXIBLE SECTOR-ERASE ARCHITECTURE on FLASH MEMORY

- One 16 K byte, two 8 K bytes, one 32 K byte, and thirty one 64 K bytes.

Individual-sector, multiple-sector, or bulk-erase capability.

| Sector Size | Address Range |
|-------------|--------------------|
| 64 Kbytes | 00000H to 0FFFFH |
| 64 Kbytes | 10000H to 1FFFFH |
| 64 Kbytes | 20000H to 2FFFFH |
| 64 Kbytes | 30000H to 3FFFFH |
| 64 Kbytes | 40000H to 4FFFFH |
| 64 Kbytes | 50000H to 5FFFFH |
| 64 Kbytes | 60000H to 6FFFFH |
| 64 Kbytes | 70000H to 7FFFFH |
| 64 Kbytes | 80000H to 8FFFFH |
| 64 Kbytes | 90000H to 9FFFFH |
| 64 Kbytes | A0000H to AFFFFH |
| 64 Kbytes | B0000H to BFFFFH |
| 64 Kbytes | C0000H to CFFFFH |
| 64 Kbytes | D0000H to DFFFFH |
| 64 Kbytes | E0000H to EFFFFH |
| 64 Kbytes | F0000H to FFFFFH |
| 64 Kbytes | 100000H to 10FFFFH |
| 64 Kbytes | 110000H to 11FFFFH |
| 64 Kbytes | 120000H to 12FFFFH |
| 64 Kbytes | 130000H to 13FFFFH |
| 64 Kbytes | 140000H to 14FFFFH |
| 64 Kbytes | 150000H to 15FFFFH |
| 64 Kbytes | 160000H to 16FFFFH |
| 64 Kbytes | 170000H to 17FFFFH |
| 64 Kbytes | 180000H to 18FFFFH |
| 64 Kbytes | 190000H to 19FFFFH |
| 64 Kbytes | 1A0000H to 1AFFFFH |
| 64 Kbytes | 1B0000H to 1BFFFFH |
| 64 Kbytes | 1C0000H to 1CFFFFH |
| 64 Kbytes | 1D0000H to 1DFFFFH |
| 64 Kbytes | 1E0000H to 1EFFFFH |
| 32 Kbytes | 1F0000H to 1F7FFFH |
| 8 Kbytes | 1F8000H to 1F9FFFH |
| 8 Kbytes | 1FA000H to 1FBFFFH |
| 16 Kbytes | 1FC000H to 1FFFFFH |

MB84VA2100 Sector Architecture

| Sector Size | Address Range |
|-------------|--------------------|
| 16 Kbytes | 00000H to 03FFFFH |
| 8 Kbytes | 04000H to 05FFFFH |
| 8 Kbytes | 06000H to 07FFFFH |
| 32 Kbytes | 08000H to 0FFFFH |
| 64 Kbytes | 10000H to 1FFFFH |
| 64 Kbytes | 20000H to 2FFFFH |
| 64 Kbytes | 30000H to 3FFFFH |
| 64 Kbytes | 40000H to 4FFFFH |
| 64 Kbytes | 50000H to 5FFFFH |
| 64 Kbytes | 60000H to 6FFFFH |
| 64 Kbytes | 70000H to 7FFFFH |
| 64 Kbytes | 80000H to 8FFFFH |
| 64 Kbytes | 90000H to 9FFFFH |
| 64 Kbytes | A0000H to AFFFFH |
| 64 Kbytes | B0000H to BFFFFH |
| 64 Kbytes | C0000H to CFFFFH |
| 64 Kbytes | D0000H to DFFFFH |
| 64 Kbytes | E0000H to EFFFFH |
| 64 Kbytes | F0000H to FFFFFH |
| 64 Kbytes | 100000H to 10FFFFH |
| 64 Kbytes | 110000H to 11FFFFH |
| 64 Kbytes | 120000H to 12FFFFH |
| 64 Kbytes | 130000H to 13FFFFH |
| 64 Kbytes | 140000H to 14FFFFH |
| 64 Kbytes | 150000H to 15FFFFH |
| 64 Kbytes | 160000H to 16FFFFH |
| 64 Kbytes | 170000H to 17FFFFH |
| 64 Kbytes | 180000H to 18FFFFH |
| 64 Kbytes | 190000H to 19FFFFH |
| 64 Kbytes | 1A0000H to 1AFFFFH |
| 64 Kbytes | 1B0000H to 1BFFFFH |
| 64 Kbytes | 1C0000H to 1CFFFFH |
| 64 Kbytes | 1D0000H to 1DFFFFH |
| 64 Kbytes | 1E0000H to 1EFFFFH |
| 64 Kbytes | 1F0000H to 1FFFFFH |

MB84VA2101 Sector Architecture

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Table 3 Sector Address Tables (MB84VA2100)

| Sector Address | A ₂₀ | A ₁₉ | A ₁₈ | A ₁₇ | A ₁₆ | A ₁₅ | A ₁₄ | A ₁₃ | Address Range |
|----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|--------------------|
| SA0 | 0 | 0 | 0 | 0 | 0 | X | X | X | 00000H to 0FFFFH |
| SA1 | 0 | 0 | 0 | 0 | 1 | X | X | X | 10000H to 1FFFFH |
| SA2 | 0 | 0 | 0 | 1 | 0 | X | X | X | 20000H to 2FFFFH |
| SA3 | 0 | 0 | 0 | 1 | 1 | X | X | X | 30000H to 3FFFFH |
| SA4 | 0 | 0 | 1 | 0 | 0 | X | X | X | 40000H to 4FFFFH |
| SA5 | 0 | 0 | 1 | 0 | 1 | X | X | X | 50000H to 5FFFFH |
| SA6 | 0 | 0 | 1 | 1 | 0 | X | X | X | 60000H to 6FFFFH |
| SA7 | 0 | 0 | 1 | 1 | 1 | X | X | X | 70000H to 7FFFFH |
| SA8 | 0 | 1 | 0 | 0 | 0 | X | X | X | 80000H to 8FFFFH |
| SA9 | 0 | 1 | 0 | 0 | 1 | X | X | X | 90000H to 9FFFFH |
| SA10 | 0 | 1 | 0 | 1 | 0 | X | X | X | A0000H to AFFFFH |
| SA11 | 0 | 1 | 0 | 1 | 1 | X | X | X | B0000H to BFFFFH |
| SA12 | 0 | 1 | 1 | 0 | 0 | X | X | X | C0000H to CFFFFH |
| SA13 | 0 | 1 | 1 | 0 | 1 | X | X | X | D0000H to DFFFFH |
| SA14 | 0 | 1 | 1 | 1 | 0 | X | X | X | E0000H to EFFFFH |
| SA15 | 0 | 1 | 1 | 1 | 1 | X | X | X | F0000H to FFFFFH |
| SA16 | 1 | 0 | 0 | 0 | 0 | X | X | X | 100000H to 10FFFFH |
| SA17 | 1 | 0 | 0 | 0 | 1 | X | X | X | 110000H to 11FFFFH |
| SA18 | 1 | 0 | 0 | 1 | 0 | X | X | X | 120000H to 12FFFFH |
| SA19 | 1 | 0 | 0 | 1 | 1 | X | X | X | 130000H to 13FFFFH |
| SA20 | 1 | 0 | 1 | 0 | 0 | X | X | X | 140000H to 14FFFFH |
| SA21 | 1 | 0 | 1 | 0 | 1 | X | X | X | 150000H to 15FFFFH |
| SA22 | 1 | 0 | 1 | 1 | 0 | X | X | X | 160000H to 16FFFFH |
| SA23 | 1 | 0 | 1 | 1 | 1 | X | X | X | 170000H to 17FFFFH |
| SA24 | 1 | 1 | 0 | 0 | 0 | X | X | X | 180000H to 18FFFFH |
| SA25 | 1 | 1 | 0 | 0 | 1 | X | X | X | 190000H to 19FFFFH |
| SA26 | 1 | 1 | 0 | 1 | 0 | X | X | X | 1A0000H to 1AFFFFH |
| SA27 | 1 | 1 | 0 | 1 | 1 | X | X | X | 1B0000H to 1BFFFFH |
| SA28 | 1 | 1 | 1 | 0 | 0 | X | X | X | 1C0000H to 1CFFFFH |
| SA29 | 1 | 1 | 1 | 0 | 1 | X | X | X | 1D0000H to 1DFFFFH |
| SA30 | 1 | 1 | 1 | 1 | 0 | X | X | X | 1E0000H to 1EFFFFH |
| SA31 | 1 | 1 | 1 | 1 | 1 | 0 | X | X | 1F0000H to 1F7FFFH |
| SA32 | 1 | 1 | 1 | 1 | 1 | 1 | 0 | 0 | 1F8000H to 1F9FFFH |
| SA33 | 1 | 1 | 1 | 1 | 1 | 1 | 0 | 1 | 1FA000H to 1FBFFFH |
| SA34 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | X | 1FC000H to 1FFFFFH |

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Table 4 Sector Address Tables (MB84VA2101)

| Sector Address | A ₂₀ | A ₁₉ | A ₁₈ | A ₁₇ | A ₁₆ | A ₁₅ | A ₁₄ | A ₁₃ | Address Range |
|----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|--------------------|
| SA0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | X | 00000H to 03FFFFH |
| SA1 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 04000H to 05FFFFH |
| SA2 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 06000H to 07FFFFH |
| SA3 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | X | 08000H to 0FFFFH |
| SA4 | 0 | 0 | 0 | 0 | 1 | X | X | X | 10000H to 1FFFFH |
| SA5 | 0 | 0 | 0 | 1 | 0 | X | X | X | 20000H to 2FFFFH |
| SA6 | 0 | 0 | 0 | 1 | 1 | X | X | X | 30000H to 3FFFFH |
| SA7 | 0 | 0 | 1 | 0 | 0 | X | X | X | 40000H to 4FFFFH |
| SA8 | 0 | 0 | 1 | 0 | 1 | X | X | X | 50000H to 5FFFFH |
| SA9 | 0 | 0 | 1 | 1 | 0 | X | X | X | 60000H to 6FFFFH |
| SA10 | 0 | 0 | 1 | 1 | 1 | X | X | X | 70000H to 7FFFFH |
| SA11 | 0 | 1 | 0 | 0 | 0 | X | X | X | 80000H to 8FFFFH |
| SA12 | 0 | 1 | 0 | 0 | 1 | X | X | X | 90000H to 9FFFFH |
| SA13 | 0 | 1 | 0 | 1 | 0 | X | X | X | A0000H to AFFFFH |
| SA14 | 0 | 1 | 0 | 1 | 1 | X | X | X | B0000H to BFFFFH |
| SA15 | 0 | 1 | 1 | 0 | 0 | X | X | X | C0000H to CFFFFH |
| SA16 | 0 | 1 | 1 | 0 | 1 | X | X | X | D0000H to DFFFFH |
| SA17 | 0 | 1 | 1 | 1 | 0 | X | X | X | E0000H to EFFFFH |
| SA18 | 0 | 1 | 1 | 1 | 1 | X | X | X | F0000H to FFFFFH |
| SA19 | 1 | 0 | 0 | 0 | 0 | X | X | X | 100000H to 10FFFFH |
| SA20 | 1 | 0 | 0 | 0 | 1 | X | X | X | 110000H to 11FFFFH |
| SA21 | 1 | 0 | 0 | 1 | 0 | X | X | X | 120000H to 12FFFFH |
| SA22 | 1 | 0 | 0 | 1 | 1 | X | X | X | 130000H to 13FFFFH |
| SA23 | 1 | 0 | 1 | 0 | 0 | X | X | X | 140000H to 14FFFFH |
| SA24 | 1 | 0 | 1 | 0 | 1 | X | X | X | 150000H to 15FFFFH |
| SA25 | 1 | 0 | 1 | 1 | 0 | X | X | X | 160000H to 16FFFFH |
| SA26 | 1 | 0 | 1 | 1 | 1 | X | X | X | 170000H to 17FFFFH |
| SA27 | 1 | 1 | 0 | 0 | 0 | X | X | X | 180000H to 18FFFFH |
| SA28 | 1 | 1 | 0 | 0 | 1 | X | X | X | 190000H to 19FFFFH |
| SA29 | 1 | 1 | 0 | 1 | 0 | X | X | X | 1A0000H to 1AFFFFH |
| SA30 | 1 | 1 | 0 | 1 | 1 | X | X | X | 1B0000H to 1BFFFFH |
| SA31 | 1 | 1 | 1 | 0 | 0 | X | X | X | 1C0000H to 1CFFFFH |
| SA32 | 1 | 1 | 1 | 0 | 1 | X | X | X | 1D0000H to 1DFFFFH |
| SA33 | 1 | 1 | 1 | 1 | 0 | X | X | X | 1E0000H to 1EFFFFH |
| SA34 | 1 | 1 | 1 | 1 | 1 | X | X | X | 1F0000H to 1FFFFH |

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Table 5.1 Flash Memory Autoselect Code

| Type | | A ₁₂ | A ₆ | A ₁ | A ₀ | Code (HEX) |
|---------------------|------------|-----------------|-----------------|-----------------|-----------------|------------|
| Manufacturer's Code | | V _{IL} | V _{IL} | V _{IL} | V _{IL} | 04H |
| Device Code | MB84VA2100 | V _{IL} | V _{IL} | V _{IL} | V _{IH} | C4H |
| | MB84VA2101 | V _{IL} | V _{IL} | V _{IL} | V _{IH} | 49H |

Table 5.2 Expanded Autoselect Code Table

| Type | | Code | DQ ₇ | DQ ₆ | DQ ₅ | DQ ₄ | DQ ₃ | DQ ₂ | DQ ₁ | DQ ₀ |
|---------------------|------------|------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|-----------------|
| Manufacturer's Code | | 04H | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 0 |
| Device Code | MB84VA2100 | C4H | 1 | 1 | 0 | 0 | 0 | 1 | 0 | 0 |
| | MB84VA2101 | 49H | 0 | 1 | 0 | 0 | 1 | 0 | 0 | 1 |

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Table 6 Flash Memory Command Definitions

| Command Sequence | Bus Write Cycles Req'd | First Bus Write Cycle | | Second Bus Write Cycle | | Third Bus Write Cycle | | Fourth Bus Read/Write Cycle | | Fifth Bus Write Cycle | | Sixth Bus Write Cycle | |
|-----------------------------|---|-----------------------|------|------------------------|------|-----------------------|------|-----------------------------|------|-----------------------|------|-----------------------|------|
| | | Addr. | Data | Addr. | Data | Addr. | Data | Addr. | Data | Addr. | Data | Addr. | Data |
| Read/Reset | 1 | XXXH | F0H | — | — | — | — | — | — | — | — | — | — |
| Read/Reset | 3 | 555H | AAH | 2AAH | 55H | 555H | F0H | RA | RD | — | — | — | — |
| Autoselect | 3 | 555H | AAH | 2AAH | 55H | 555H | 90H | — | — | — | — | — | — |
| Program | 4 | 555H | AAH | 2AAH | 55H | 555H | A0H | PA | PD | — | — | — | — |
| Chip Erase | 6 | 555H | AAH | 2AAH | 55H | 555H | 80H | 555H | AAH | 2AAH | 55H | 555H | 10H |
| Sector Erase | 6 | 555H | AAH | 2AAH | 55H | 555H | 80H | 555H | AAH | 2AAH | 55H | SA | 30H |
| Sector Erase Suspend | Erase can be suspended during sector erase with Addr ("H" or "L"). Data (B0H) | | | | | | | | | | | | |
| Sector Erase Resume | Erase can be resumed after suspend with Addr ("H" or "L"). Data (30H) | | | | | | | | | | | | |
| Set to Fast Mode | 3 | 555H | AAH | 2AAH | 55H | 555H | 20H | — | — | — | — | — | — |
| Fast Program (Note) | 2 | XXXH | A0H | PA | PD | — | — | — | — | — | — | — | — |
| Reset from Fast Mode (Note) | 2 | XXXH | 90H | XXXH | F0H | — | — | — | — | — | — | — | — |
| Extended Sector Protect | 4 | XXXH | 60H | SPA | 60H | SPA | 40H | SPA | SD | — | — | — | — |

Address bits A₁₁ to A₂₀ = X = "H" or "L" for all address commands except for Program Address (PA) and Sector Address (SA).

Bus operations are defined in Table 2.

Both Read/Reset commands are functionally equivalent, resetting the device to the read mode.

RA =Address of the memory location to be read.

PA =Address of the memory location to be programmed. Addresses are latched on the falling edge of the write pulse.

SA =Address of the sector to be erased. The combination of A₂₀, A₁₉, A₁₈, A₁₇, A₁₆, A₁₅, A₁₄, and A₁₃ will uniquely select any sector.

RD =Data read from location RA during read operation.

PD =Data to be programmed at location PA.

SPA =Sector address to be protected. Set sector address (SA) and (A₆, A₁, A₀) = (0, 1, 0).

SD =Sector protection verify data. Output 01H at protected sector addresses and output 00H at unprotected sector addresses.

Note:This command is valid while Fast Mode.

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■ ABSOLUTE MAXIMUM RATINGS

| | |
|--|-----------------------------|
| Storage Temperature | -55°C to +125°C |
| Ambient Temperature with Power Applied | -25°C to +85°C |
| Voltage with Respect to Ground All pins (Note) | -0.3 V to $V_{ccf} + 0.5$ V |
| | -0.3 V to $V_{ccs} + 0.5$ V |
| V_{ccf}/V_{ccs} Supply (Note) | -0.3 V to +4.6 V |

Note: Minimum DC voltage on input or I/O pins are -0.5 V. During voltage transitions, inputs may negative overshoot V_{ss} to -2.0 V for periods of up to 20 ns. Maximum DC voltage on output and I/O pins are $V_{ccf} + 0.5$ V or $V_{ccs} + 0.5$ V. During voltage transitions, outputs may positive overshoot to $V_{cc} + 2.0$ V for periods of up to 20 ns.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum rating conditions. Do not exceed these ratings.

■ RECOMMENDED OPERATING RANGES

| | |
|--|------------------|
| Commercial Devices | |
| Ambient Temperature (T_A) | -20°C to +85°C |
| V_{ccf}/V_{ccs} Supply Voltages..... | +2.7 V to +3.6 V |

Operating ranges define those limits between which the functionality of the device is guaranteed.

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

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■ DC CHARACTERISTICS

| Parameter Symbol | Parameter Description | Test Conditions | | Min. | Typ. | Max. | Unit | |
|---------------------|--|--|----------------------------------|-------------------------------|------|-----------------------|------|----|
| I _{LI} | Input Leakage Current | — | | -1.0 | — | +1.0 | μA | |
| I _{LO} | Output Leakage Current | — | | -1.0 | — | +1.0 | μA | |
| I _{CC1f} | Flash V _{CC} Active Current (Read) | V _{CCf} = V _{CC} Max., \overline{CEf} = V _{IL} OE = V _{IH} | t _{CYCLE} = 10 MHz | — | — | 30 | mA | |
| | | | t _{CYCLE} = 5 MHz | — | — | 15 | | |
| I _{CC2f} | Flash V _{CC} Active Current (Program/Erase) | V _{CCf} = V _{CC} Max., \overline{CEf} = V _{IL} , OE = V _{IH} | | — | — | 35 | mA | |
| I _{CC1S} | SRAM V _{CC} Active Current | V _{CCS} = V _{CC} Max., CE1s = V _{IL} , CE2s = V _{IH} | t _{CYCLE} = 10 MHz | — | — | 40 | mA | |
| | | | t _{CYCLE} = 1 MHz | — | — | 12 | mA | |
| I _{CC2S} | SRAM V _{CC} Active Current | CE1s = 0.2 V, CE2s = V _{CCS} - 0.2 V, WE = V _{CCS} - 0.2 V | t _{CYCLE} = 10 MHz | — | — | 35 | mA | |
| | | | t _{CYCLE} = 1 MHz | — | — | 6 | mA | |
| I _{SB1f} | Flash V _{CC} Standby Current | V _{CCf} = V _{CC} Max., \overline{CEf} = V _{CCf} ± 0.3 V RESET = V _{CCf} ± 0.3 V | | — | — | 5 | μA | |
| I _{SB2f} | Flash V _{CC} Standby Current (RESET) | V _{CCf} = V _{CC} Max., RESET = V _{SS} ± 0.3 V | | — | — | 5 | μA | |
| I _{SB1S} | SRAM V _{CC} Standby Current | CE1s = V _{IH} or CE2s = V _{IL} | | — | — | 2 | mA | |
| I _{SB2S**} | SRAM V _{CC} Standby Current | CE1s = V _{CC} - 0.2 V or CE2s = 0.2 V | V _{CCS} = 3.0 V ± 10% | T _A = 25°C | — | 1 | 2.5 | μA |
| | | | | T _A = -20 to +85°C | — | — | 55 | μA |
| | | | V _{CCS} = 3.3 V ± 0.3 V | T _A = 25°C | — | 1.5 | 3 | μA |
| | | | | T _A = -20 to +85°C | — | — | 60 | μA |
| | | | V _{CCS} = 3.0 V | T _A = 25°C | — | 1 | 2 | μA |
| | | | | T _A = -20 to +40°C | — | — | 5 | μA |
| | | | T _A = -20 to +85°C | — | — | 50 | μA | |
| V _{IL} | Input Low Level | — | | -0.3 | — | 0.6 | V | |
| V _{IH} | Input High Level | — | | 2.2 | — | V _{CC} +0.3* | V | |
| V _{OL} | Output Low Voltage Level | I _{OL} = 2.1 mA, V _{CCf} = V _{CCS} = V _{CC} Min. | | — | — | 0.4 | V | |
| V _{OH} | Output High Voltage Level | I _{OH} = -500 μA, V _{CCf} = V _{CCS} = V _{CC} Min. | | V _{CC} -0.5 | — | — | V | |
| V _{LKO} | Flash Low V _{CC} Lock-Out Voltage | — | | 2.3 | — | 2.5 | V | |

* : V_{CC} indicate lower of V_{CCf} or V_{CCS}

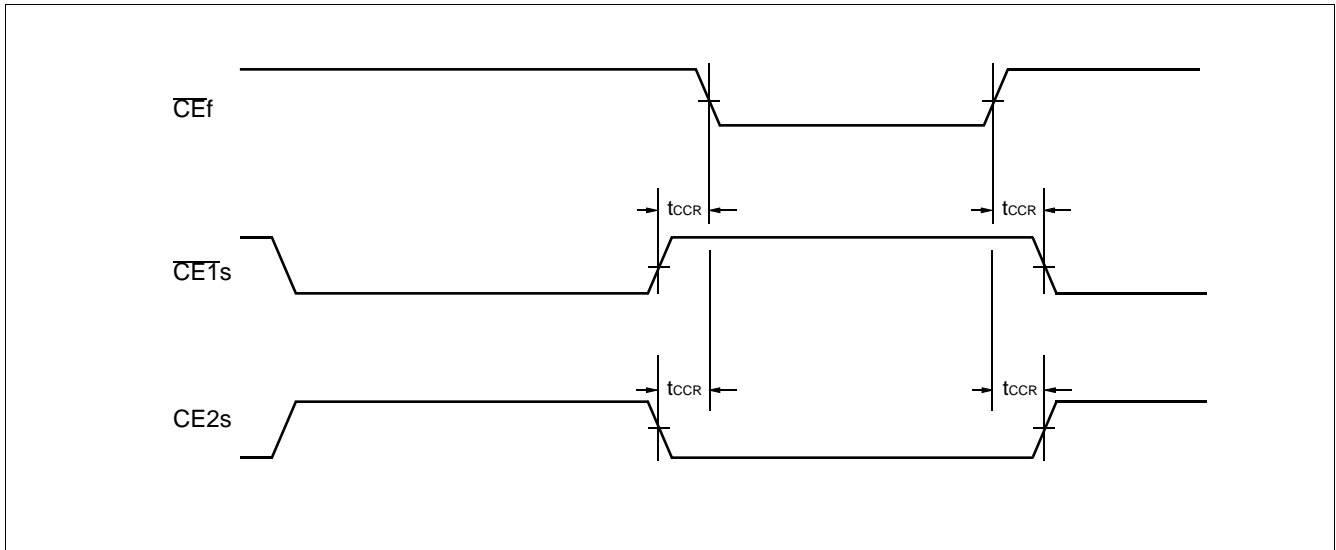
** : During standby mode with CE1s = V_{CCS} - 0.2 V, CE2s should be CE2s < 0.2V or CE2s > V_{CCS} - 0.2V

■ AC CHARACTERISTICS

• CE Timing

| Parameter Symbols | | Description | Test Setup | | -10 | Unit |
|-------------------|------------------|-----------------|------------|------|-----|------|
| JEDEC | Standard | | | | | |
| — | t _{CCR} | CE Recover Time | — | Min. | 0 | ns |

• Timing Diagram for alternating SRAM to Flash



MB84VA2100-10/MB84VA2101-10

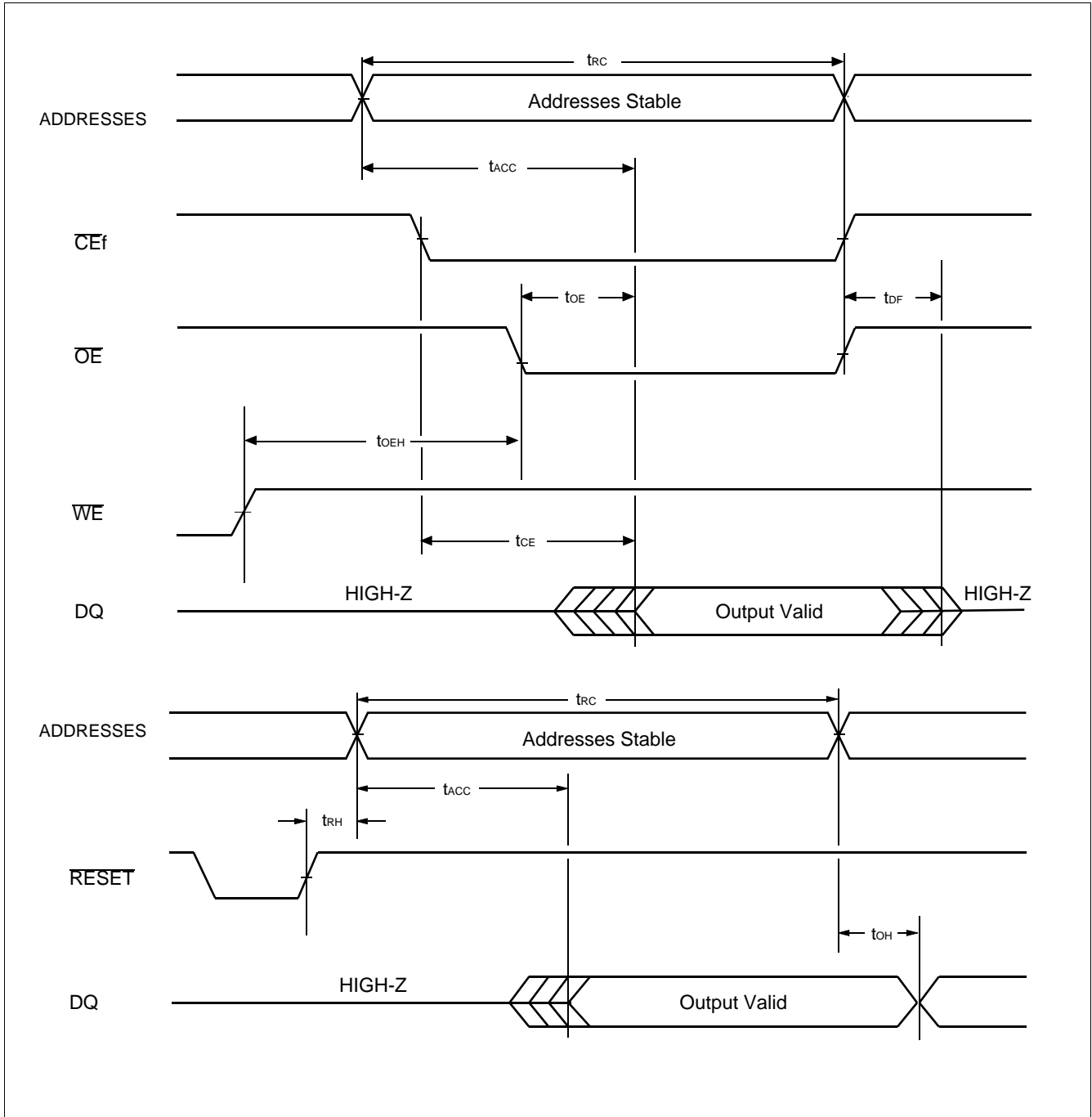
• Read Only Operations Characteristics (Flash)

| Parameter Symbols | | Description | Test Setup | -10 (Note) | | Unit |
|-------------------|--------------------|---|---|------------|------|------|
| JEDEC | Standard | | | Min. | Max. | |
| t _{AVAV} | t _{RC} | Read Cycle Time | — | 100 | — | ns |
| t _{AVQV} | t _{ACC} | Address to Output Delay | $\overline{CE}f = V_{IL}$ $\overline{OE} = V_{IL}$ | — | 100 | ns |
| t _{ELQV} | t _{CEf} | Chip Enable to Output Delay | $\overline{OE} = V_{IL}$ | — | 100 | ns |
| t _{GLQV} | t _{OE} | Output Enable to Output Delay | — | — | 40 | ns |
| t _{EHQZ} | t _{DF} | Chip Enable to Output High-Z | — | — | 30 | ns |
| t _{GHQZ} | t _{DF} | Output Enable to Output High-Z | — | — | 30 | ns |
| t _{AXQX} | t _{OH} | Output Hold Time From Addresses, $\overline{CE}f$ or \overline{OE} , Whichever Occurs First | — | 0 | — | ns |
| — | t _{READY} | RESET Pin Low to Read Mode | — | — | 20 | μs |

Note: Test Conditions—Output Load: 1 TTL gate and 30 pF
 Input rise and fall times: 5 ns
 Input pulse levels: 0.0 V to 3.0 V
 Timing measurement reference level
 Input: 1.5 V
 Output: 1.5 V

MB84VA2100-10/MB84VA2101-10

• Read Cycle (Flash)



MB84VA2100-10/MB84VA2101-10

• Erase/Program Operations (Flash)

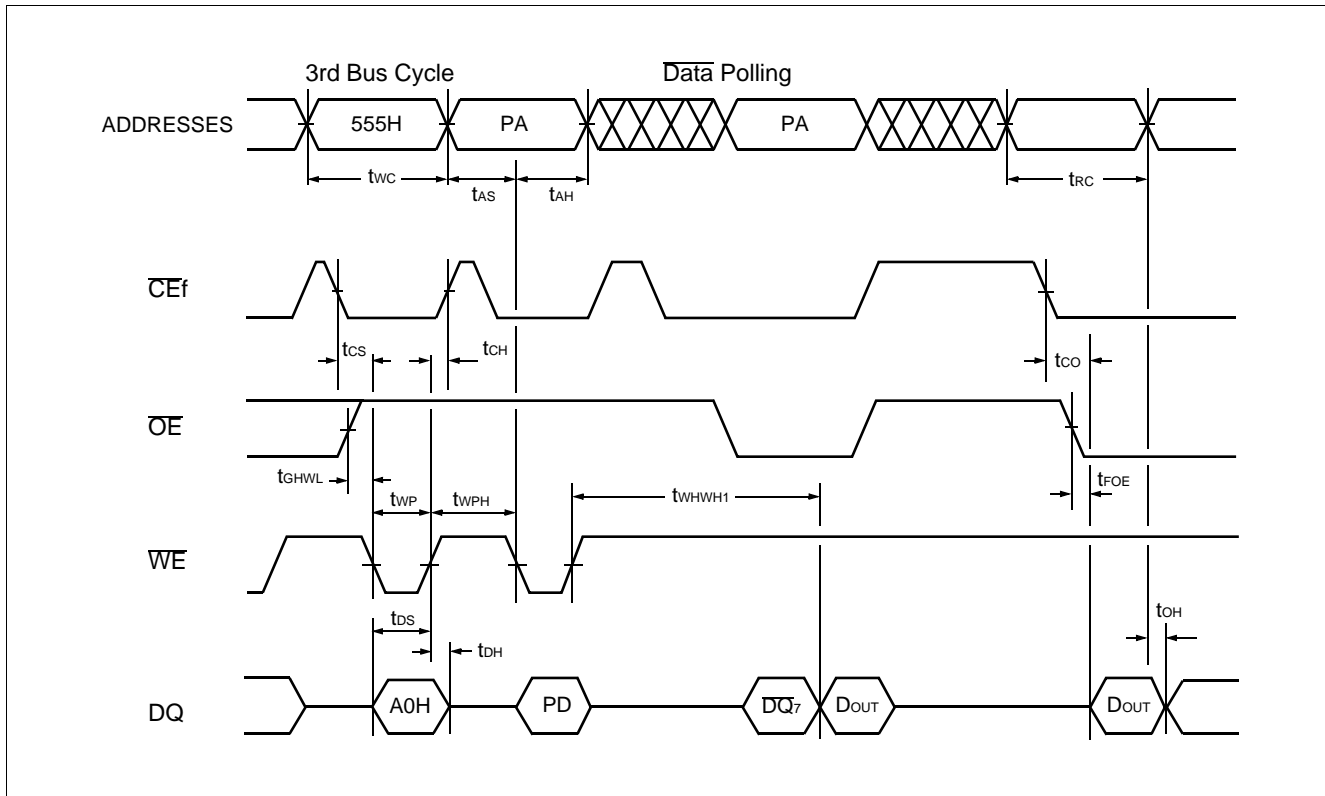
| Parameter Symbols | | Description | -10 | | | Unit |
|-------------------|----------|--|------|------|------|---------|
| JEDEC | Standard | | Min. | Typ. | Max. | |
| tAVAV | tWC | Write Cycle Time | 100 | — | — | ns |
| tAVWL | tAS | Address Setup Time (\overline{WE} to Addr.) | 0 | — | — | ns |
| tAVEL | tAS | Address Setup Time (\overline{CEf} to Addr.) | 0 | — | — | ns |
| tWLAX | tAH | Address Hold Time (\overline{WE} to Addr.) | 50 | — | — | ns |
| tELAX | tAH | Address Hold Time (\overline{CEf} to Addr.) | 50 | — | — | ns |
| tdVWH | tdS | Data Setup Time | 50 | — | — | ns |
| tWHDX | tdH | Data Hold Time | 0 | — | — | ns |
| — | toES | Output Enable Setup Time | 0 | — | — | ns |
| — | toEH | Output Enable Hold Time | 0 | — | — | ns |
| | | Read Toggle and \overline{Data} Polling | 10 | — | — | ns |
| tGHEL | tGHEL | Read Recover Time Before Write (\overline{OE} to \overline{CEf}) | 0 | — | — | ns |
| tGHWL | tGHWL | Read Recover Time Before Write (\overline{OE} to \overline{WE}) | 0 | — | — | ns |
| tWLEL | tWS | \overline{WE} Setup Time (\overline{CEf} to \overline{WE}) | 0 | — | — | ns |
| tELWL | tCS | \overline{CEf} Setup Time (\overline{WE} to \overline{CEf}) | 0 | — | — | ns |
| tEHWL | tWH | \overline{WE} Hold Time (\overline{CEf} to \overline{WE}) | 0 | — | — | ns |
| tWHEH | tCH | \overline{CEf} Hold Time (\overline{WE} to \overline{CEf}) | 0 | — | — | ns |
| tWLWH | tWP | Write Pulse Width | 50 | — | — | ns |
| tELEH | tCP | \overline{CEf} Pulse Width | 50 | — | — | ns |
| tWHWL | tWPH | Write Pulse Width High | 30 | — | — | ns |
| tEHEL | tCPH | \overline{CEf} Pulse Width High | 30 | — | — | ns |
| tWHWH1 | tWHWH1 | Byte Programming Operation | — | 8 | — | μ s |
| tWHWH2 | tWHWH2 | Sector Erase Operation (Note 1) | — | 1 | — | sec |
| | | | — | — | 15 | sec |
| — | tVCS | Vccf Setup Time | 50 | — | — | μ s |
| — | tVLHT | Voltage Transition Time (Note 2) | 4 | — | — | μ s |
| — | tVIDR | Rise Time to V _{ID} (Note 2) | 500 | — | — | ns |
| — | tRB | Recover Time from RY/BY | 0 | — | — | ns |
| — | tRP | RESET Pulse Width | 500 | — | — | ns |
| — | tRH | RESET Hold Time Before Read | 200 | — | — | ns |
| — | tEOE | Delay Time from Embedded Output Enable | — | — | 100 | ns |
| — | tBUSY | Program/Erase Valid to RY/BY Delay | — | — | 90 | ns |

Note : 1. This does not include the preprogramming time.

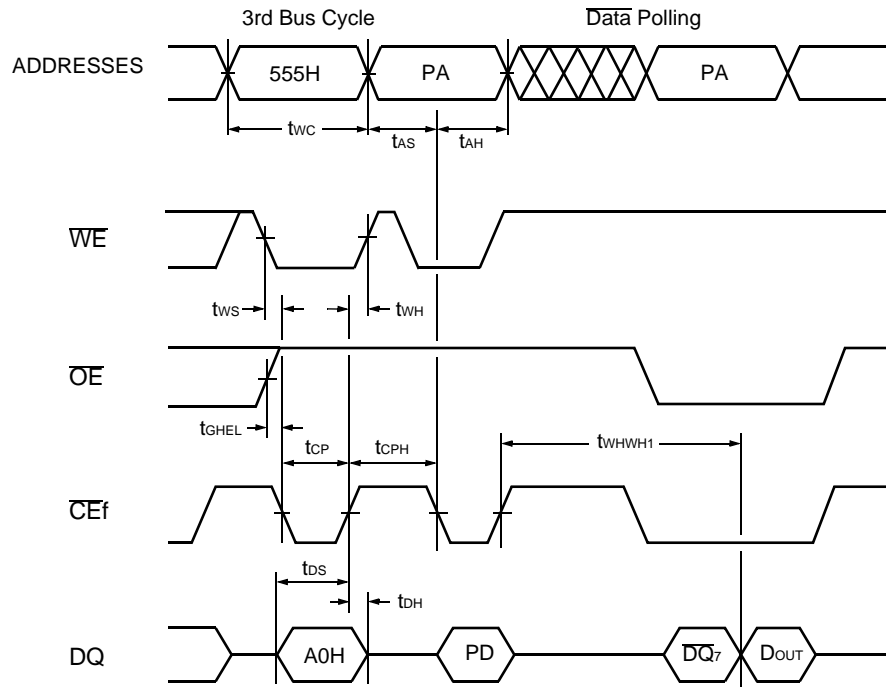
2. This timing is for Sector Protection Operation.

MB84VA2100-10/MB84VA2101-10

• Write Cycle (\overline{WE} control) (Flash)



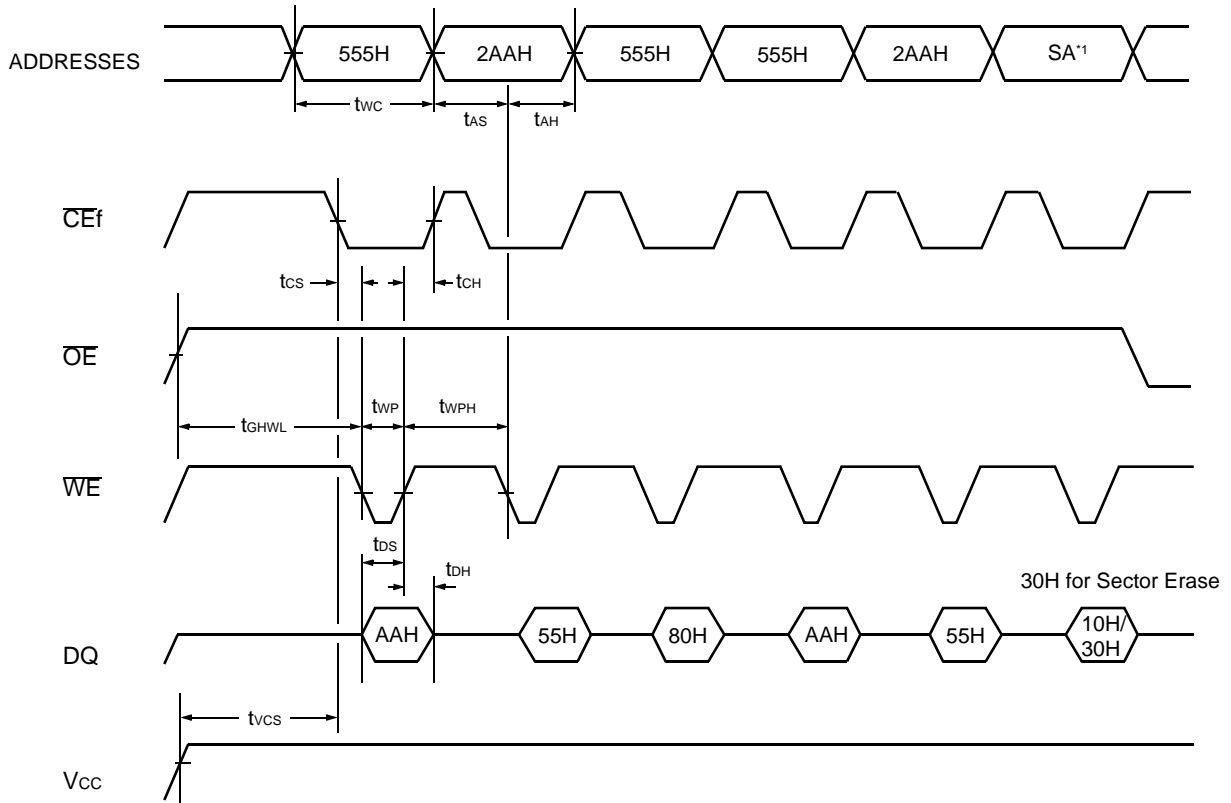
• Write Cycle (\overline{CEf} control) (Flash)



- Notes:**
1. PA is address of the memory location to be programmed.
 2. PD is data to be programmed at byte address.
 3. $\overline{DQ_7}$ is the output of the complement of the data written to the device.
 4. D_{OUT} is the output of the data written to the device.
 5. Figure indicates last two bus cycles out of four bus cycle sequence.

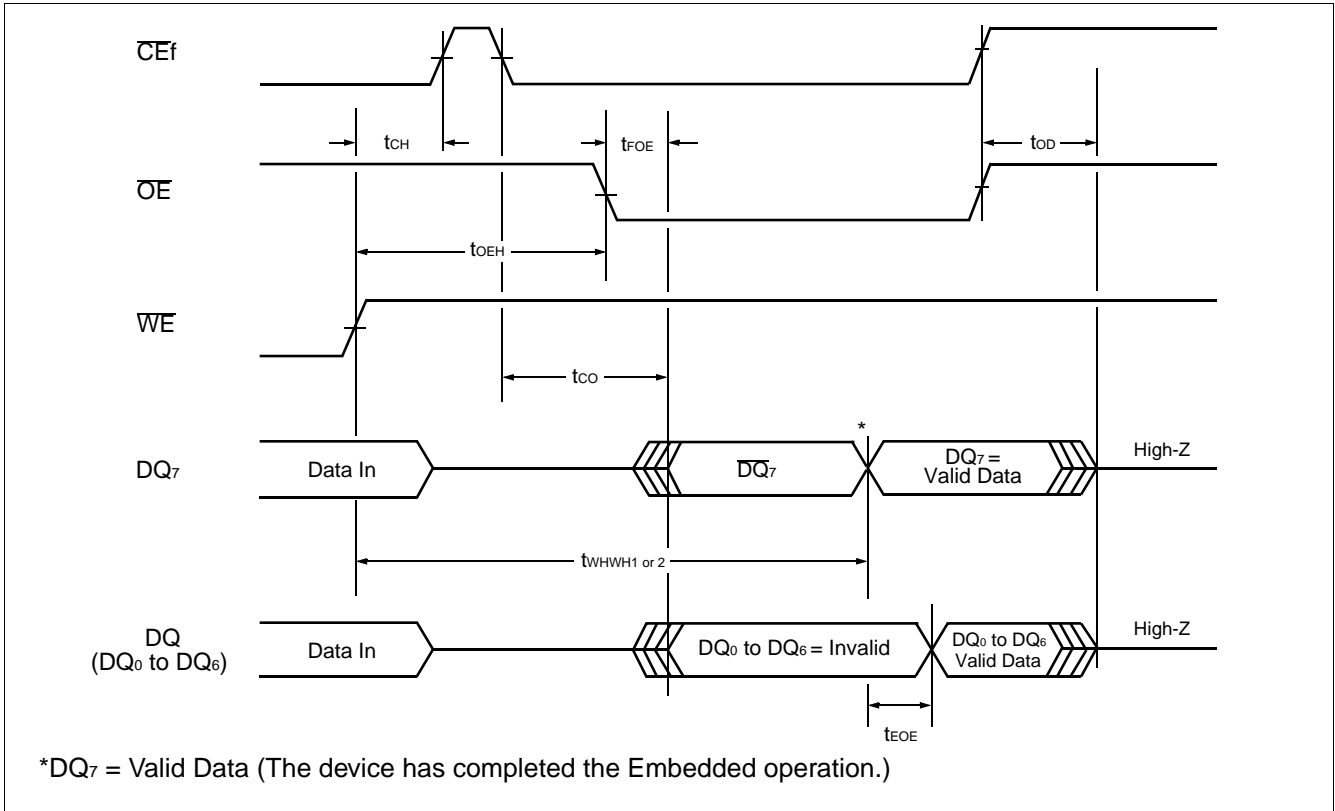
MB84VA2100-10/MB84VA2101-10

• AC Waveforms Chip/Sector Erase Operations (Flash)

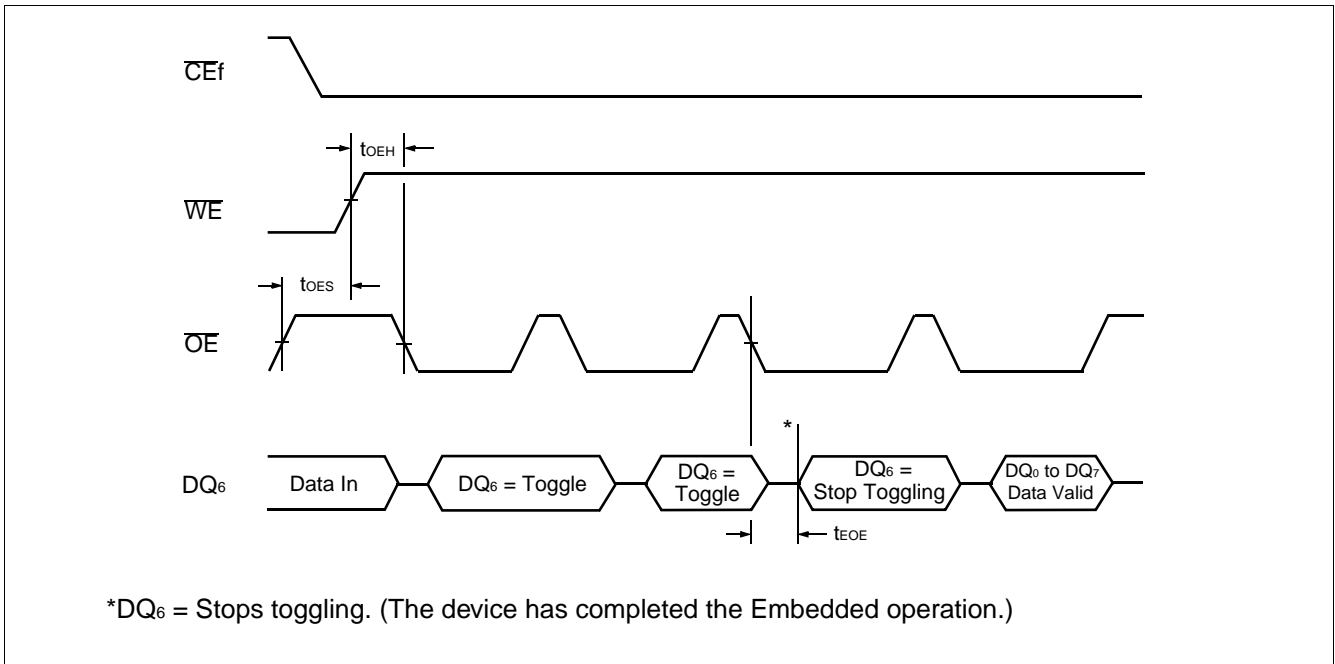


Note: 1. SA is the sector address for Sector Erase. Addresses = 555H for Chip Erase.

• AC Waveforms for Data Polling during Embedded Algorithm Operations (Flash)

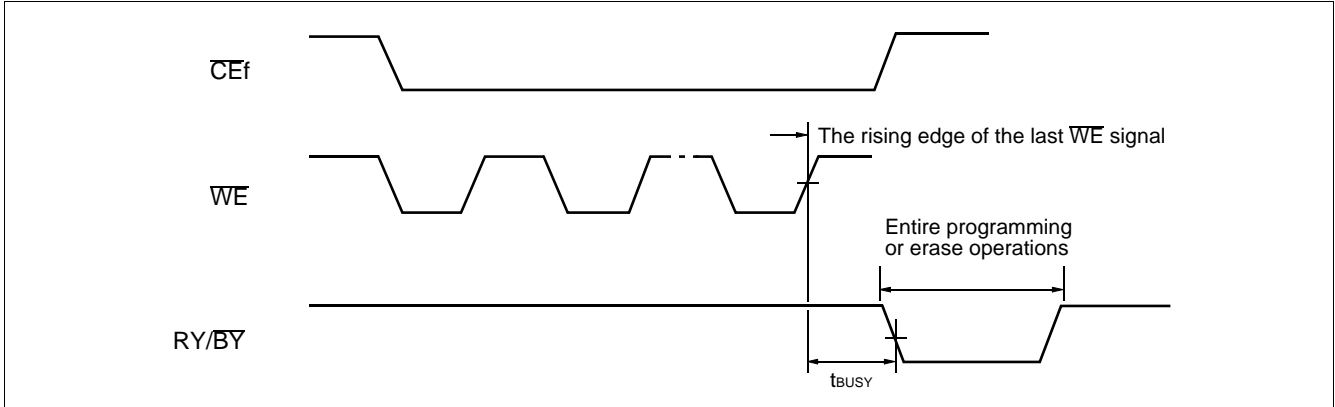


• AC Waveforms for Taggle Bit during Embedded Algorithm Operations (Flash)

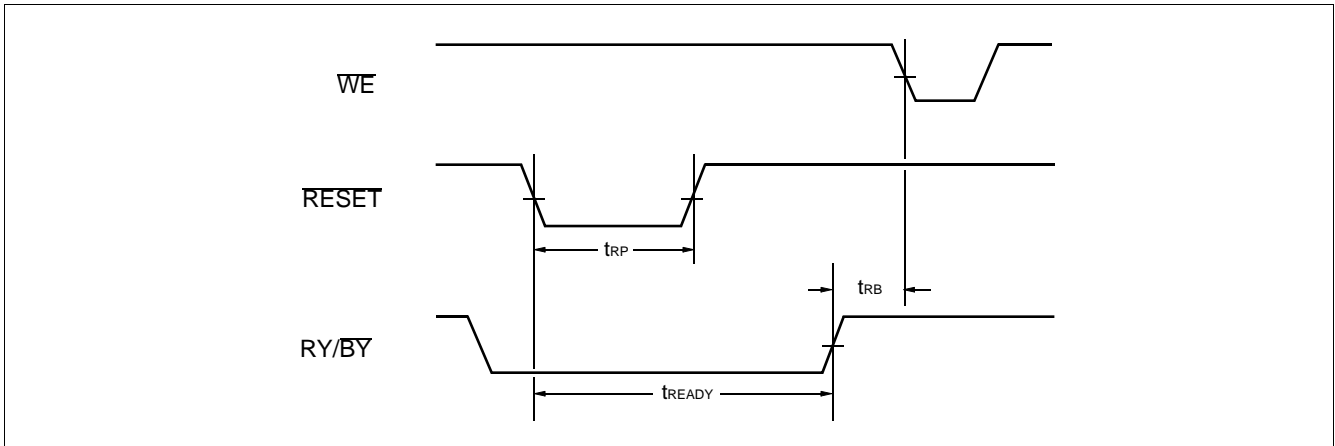


MB84VA2100-10/MB84VA2101-10

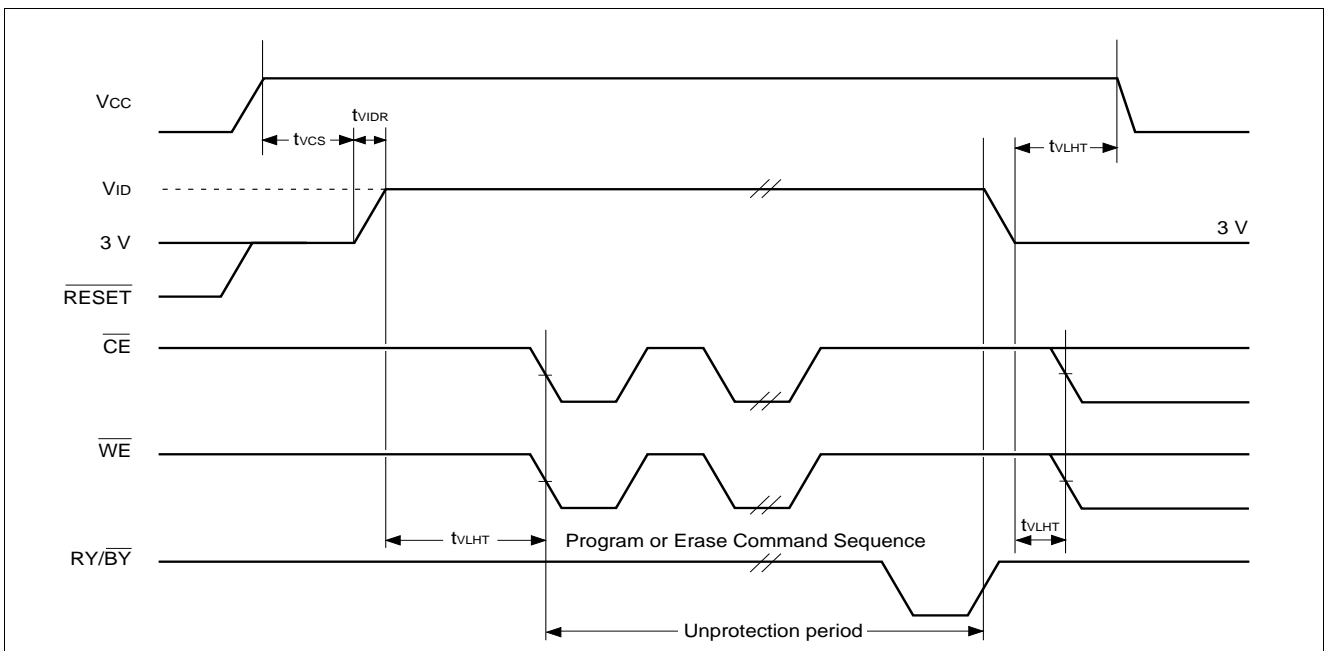
• RY/BY Timing Diagram during Write/Erase Operations (Flash)



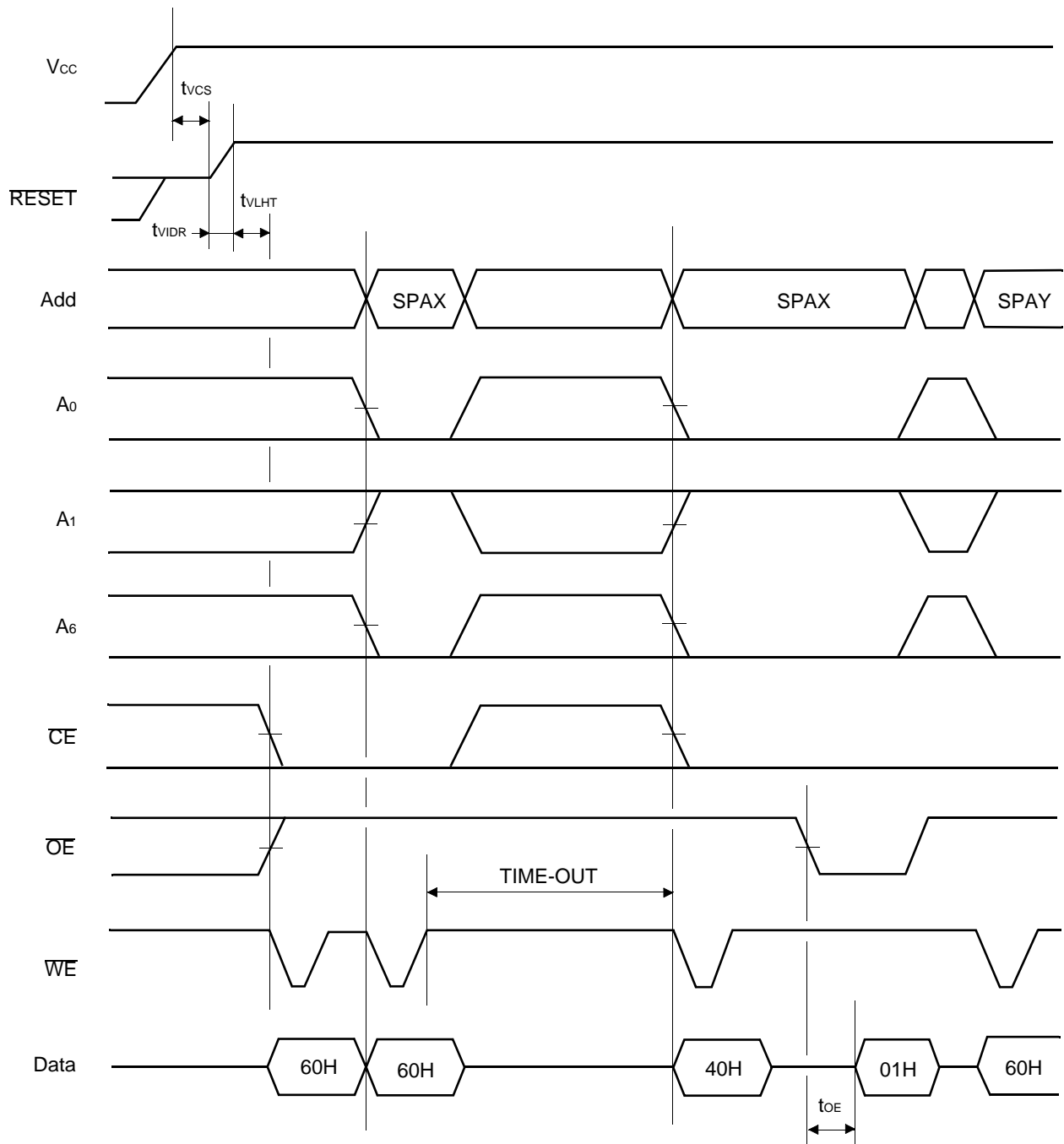
• RESET, RY/BY Timing Diagram (Flash)



• Temporary Sector Unprotection (Flash)



• Extended Sector Protection (Flash)



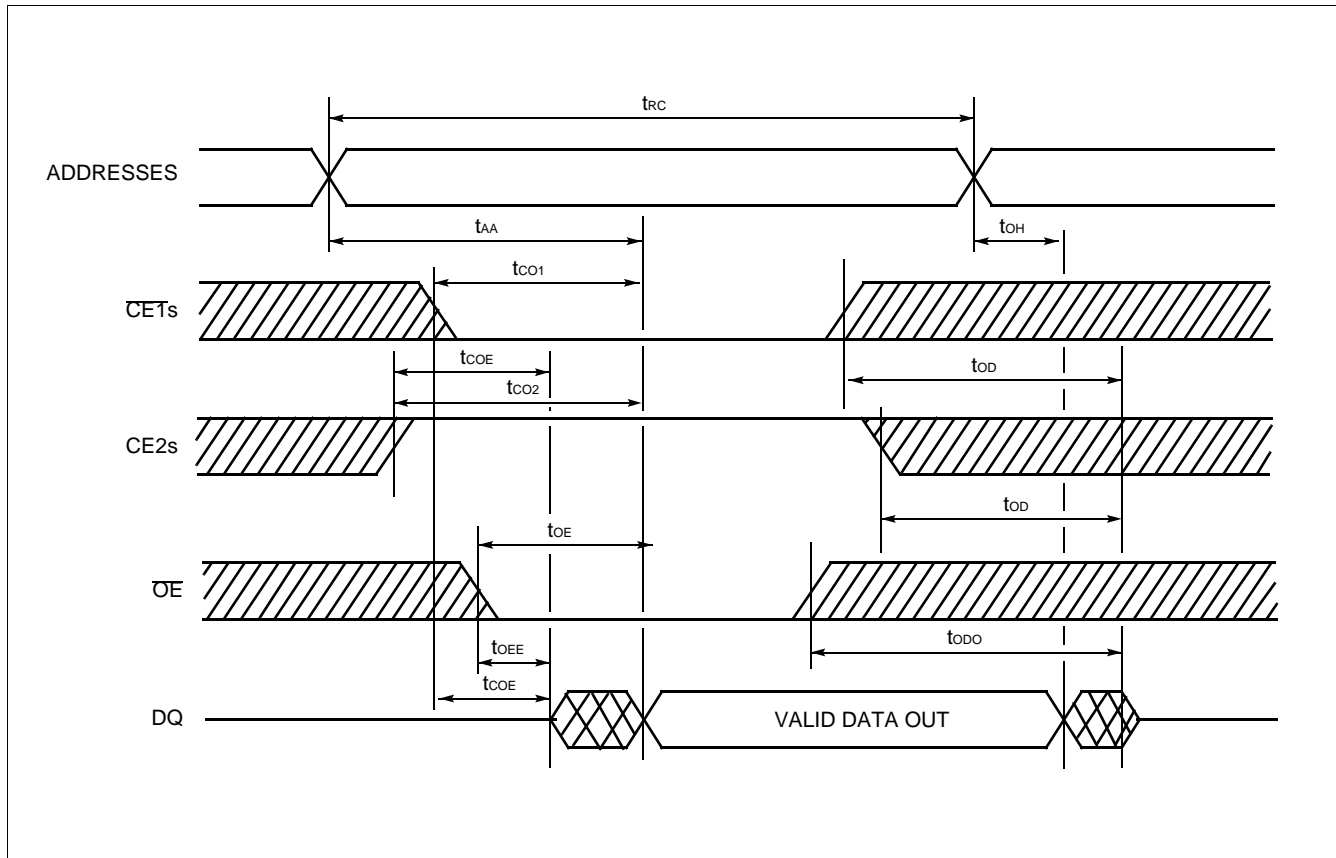
SPAX : Sector Address to be protected
 SPAY : Next Sector Address to be protected
 TIME-OUT : Time-Out window = 150 μs (min)

MB84VA2100-10/MB84VA2101-10

• Read Cycle (SRAM)

| Parameter Symbol | Parameter Description | Min. | Max. | Unit |
|------------------|--|------|------|------|
| t_{RC} | Read Cycle Time | 100 | — | ns |
| t_{AA} | Address Access Time | — | 100 | ns |
| t_{CO1} | Chip Enable ($\overline{CE1}$ s) Access Time | — | 100 | ns |
| t_{CO2} | Chip Enable (CE2s) Access Time | — | 100 | ns |
| t_{OE} | Output Enable Access Time | — | 50 | ns |
| t_{COE} | Chip Enable ($\overline{CE1}$ s Low and CE2s High) to Output Active | 5 | — | ns |
| t_{OEE} | Output Enable Low to Output Active | 0 | — | ns |
| t_{OD} | Chip Enable ($\overline{CE1}$ s High or CE2s Low) to Output High-Z | — | 40 | ns |
| t_{ODO} | Output Enable High to Output High-Z | — | 40 | ns |
| t_{OH} | Output Data Hold Time | 10 | — | ns |

• Read Cycle (Note 1) (SRAM)

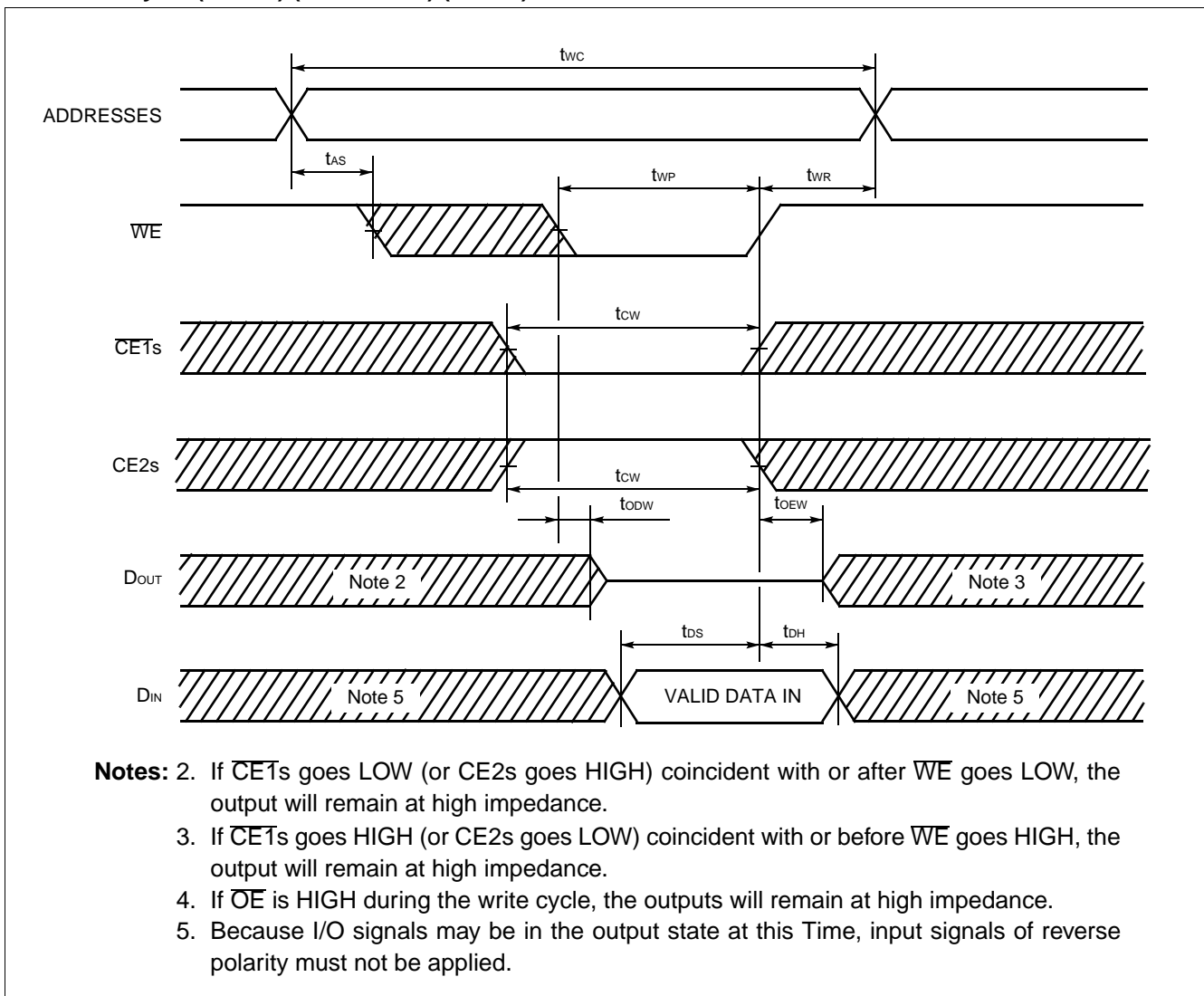


Note: 1. \overline{WE} remains HIGH for the read cycle.

• Write Cycle (SRAM)

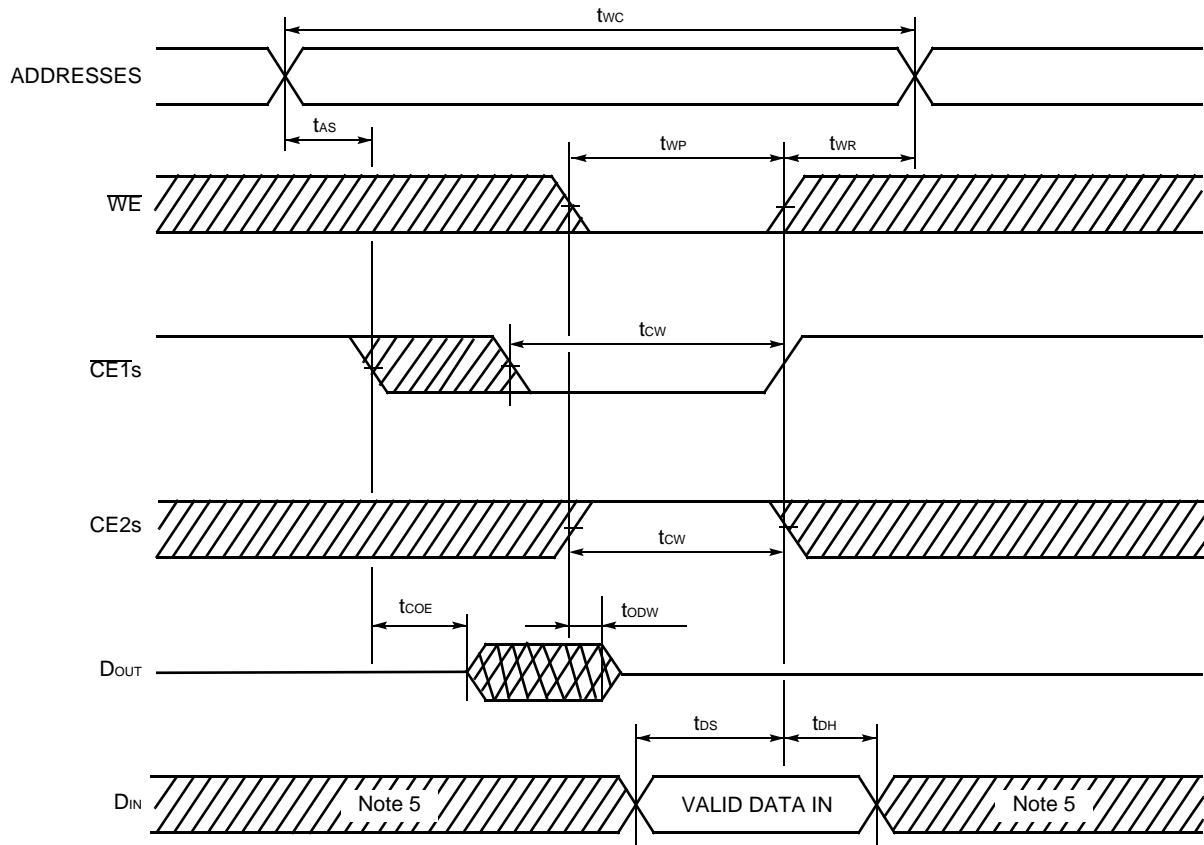
| Parameter Symbol | Parameter Description | Min. | Max. | Unit |
|------------------|-----------------------------|------|------|------|
| t_{WC} | Write Cycle Time | 100 | — | ns |
| t_{WP} | Write Pulse Width | 60 | — | ns |
| t_{CW} | Chip Enable to End of Write | 80 | — | ns |
| t_{AS} | Address Setup Time | 0 | — | ns |
| t_{WR} | Write Recovery Time | 0 | — | ns |
| t_{ODW} | WE Low to Output High-Z | — | 40 | ns |
| t_{OEW} | WE High to Output Active | 0 | — | ns |
| t_{DS} | Data Setup Time | 40 | — | ns |
| t_{DH} | Data Hold Time | 0 | — | ns |

• Write Cycle (Note 4) (WE control) (SRAM)



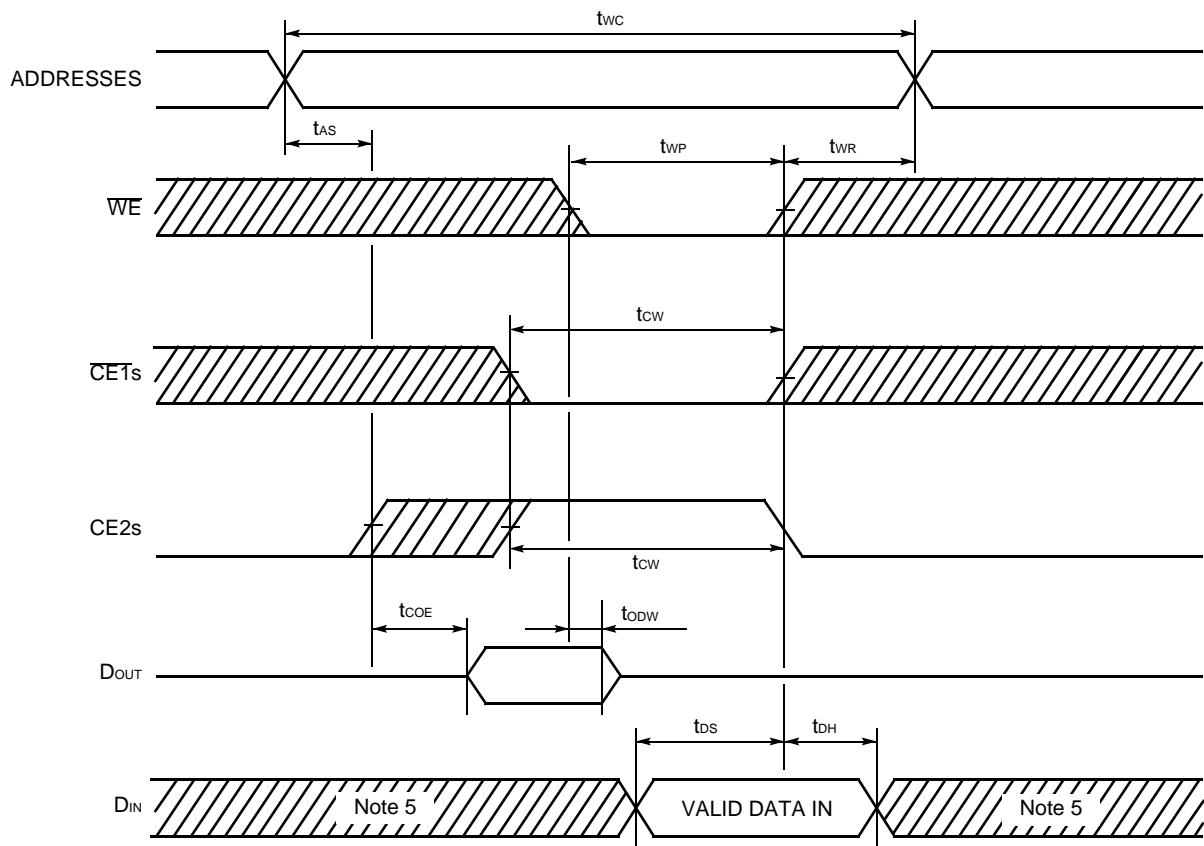
MB84VA2100-10/MB84VA2101-10

• Write Cycle (Note 4) ($\overline{CE1s}$ control) (SRAM)



- Notes:**
2. If $\overline{CE1s}$ goes LOW (or CE2s goes HIGH) coincident with or after \overline{WE} goes LOW, the output will remain at high impedance.
 3. If $\overline{CE1s}$ goes HIGH (or CE2s goes LOW) coincident with or before \overline{WE} goes HIGH, the output will remain at high impedance.
 4. If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.
 5. Because I/O signals may be in the output state at this Time, input signals of reverse polarity must not be applied.

• Write Cycle (Note 4) (CE2s Control) (SRAM)



- Notes:**
2. If $\overline{CE1s}$ goes LOW (or CE2s goes HIGH) coincident with or after \overline{WE} goes LOW, the output will remain at high impedance.
 3. If $\overline{CE1s}$ goes HIGH (or CE2s goes LOW) coincident with or before \overline{WE} goes HIGH, the output will remain at high impedance.
 4. If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.
 5. Because I/O signals may be in the output state at this Time, input signals of reverse polarity must not be applied.

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■ ERASE AND PROGRAMMING PERFORMANCE (Flash)

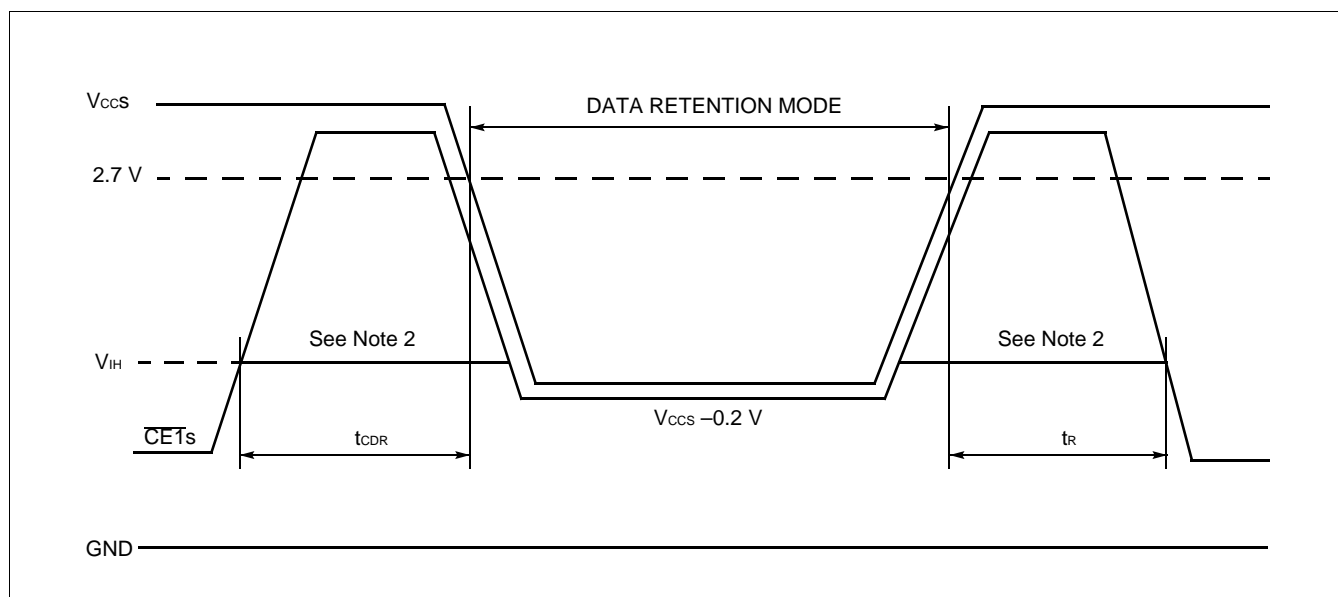
| Parameter | Limits | | | Unit | Comment |
|-----------------------|---------|------|-------|--------|--|
| | Min. | Typ. | Max. | | |
| Sector Erase Time | — | 1 | 15 | sec | Excludes programming time prior to erasure |
| Byte Programming Time | — | 8 | 3,600 | μs | Excludes system-level overhead |
| Chip Programming Time | — | 16.8 | 100 | sec | Excludes system-level overhead |
| Erase/Program Cycle | 100,000 | — | — | cycles | |

■ DATA RETENTION CHARACTERISTICS (SRAM)

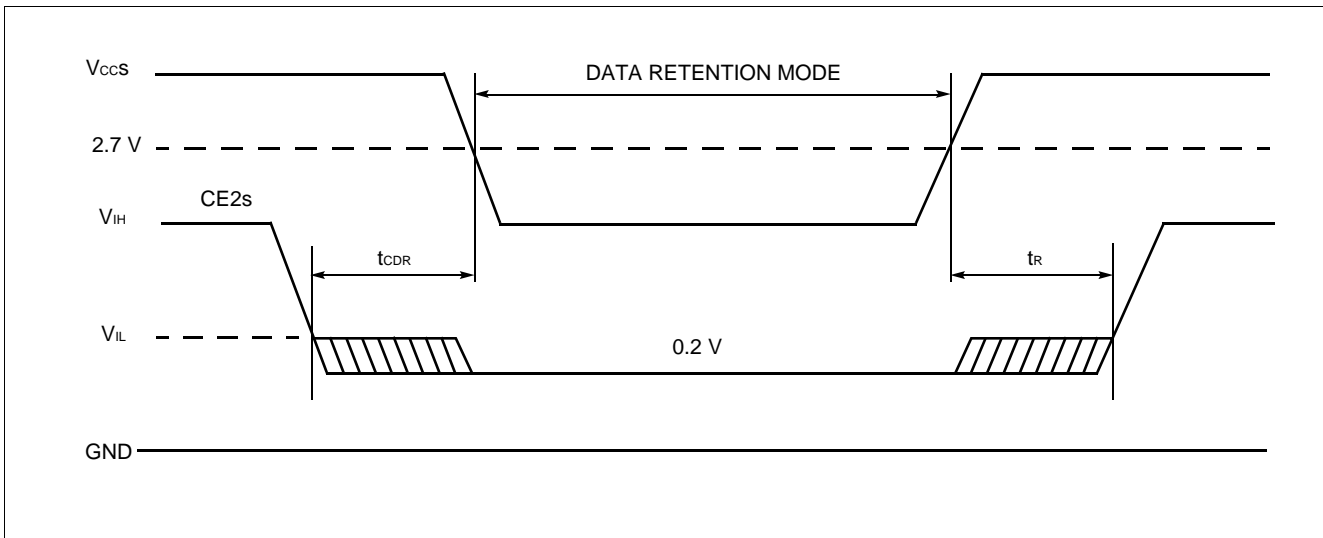
| Parameter Symbol | Parameter Description | Min. | Typ. | Max. | Unit |
|------------------|---|-------------------------|------|------|------|
| V_{DH} | Data Retention Supply Voltage | 2.0 | — | 3.6 | V |
| I_{DDs2} | Standby Current | $V_{DH} = 3.0\text{ V}$ | — | 50* | μA |
| | | $V_{DH} = 3.6\text{ V}$ | — | 60 | μA |
| t_{CDR} | Chip Deselect to Data Retention Mode Time | 0 | — | — | ns |
| t_R | Recovery Time | 5 | — | — | ms |

* : 5 μA (Max.) at $T_A = -20^\circ\text{C}$ to $+40^\circ\text{C}$

• $\overline{\text{CE}}\text{T}s$ Controlled Data Retention Mode (Note 1)



• **CE2s Controlled Data Retention Mode (Note 3)**



- Notes:**
1. In $\overline{CE1}$ s controlled data retention mode, input level of CE2s should be fixed V_{CCS} to $V_{CCS}-0.2V$ or V_{SS} to $0.2V$ during data retention mode. Other input and input/output pins can be used between $-0.3V$ to $V_{CCS}+0.3V$.
 2. When $\overline{CE1}$ s is operating at the V_{IH} min. level ($2.2V$), the standby current is given by I_{SB1S} during the transition of V_{CCS} from 3.6 to $2.2V$.
 3. In CE2s controlled data retention mode, input and input/output pins can be used between between $-0.3V$ to $V_{CCS}+0.3V$.

■ **PIN CAPACITANCE**

| Parameter Symbol | Parameter Description | Test Setup | Typ. | Max. | Unit |
|------------------|-------------------------|---------------|-------|-------|------|
| C_{IN} | Input Capacitance | $V_{IN} = 0$ | T.B.D | T.B.D | pF |
| C_{OUT} | Output Capacitance | $V_{OUT} = 0$ | T.B.D | T.B.D | pF |
| C_{IN2} | Control Pin Capacitance | $V_{IN} = 0$ | T.B.D | T.B.D | pF |

Note: Test conditions $T_A = 25^\circ C$, $f = 1.0$ MHz

Note: Test conditions $T_A = 25^\circ C$, $f = 1.0$ MHz

■ **HANDLING OF PACKAGE**

Please handle this package carefully since the sides of packages are right angle.

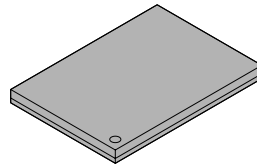
■ **CAUTION**

1.)The high voltage (VID) can not apply to address pins and control pins except **RESET**. Therefore, it can not use autoselect and sector protect function by applying the high voltage (VID) to specific pins.
2.)For the sector protection, since the high voltage (VID) can be applied to the **RESET**, it can be protected the sector using "Extended sector protect" command.

MB84VA2100-10/MB84VA2101-10

■ PACKAGE

48-pin plastic FBGA

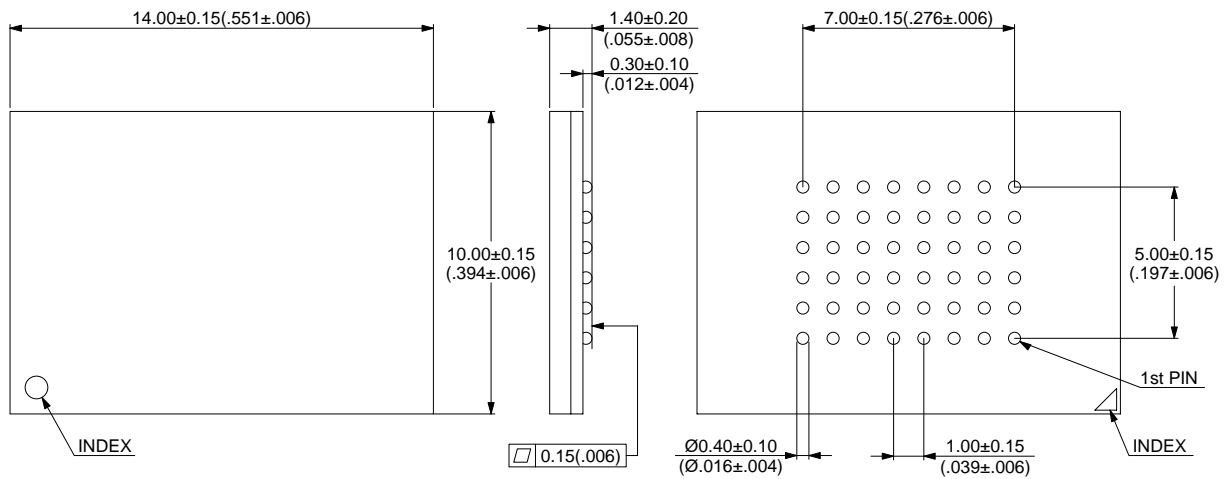


(BGA-48P-M10)

■ PACKAGE DIMENSIONS

48-pin plastic BGA
(BGA-48P-M10)

Note: The actual shape of coners may differ from the dimension.



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Dimension in mm (inches).

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